

STS32XXXXUXXX

TVS Diode ESD suppressor



Product features

- 2000 Watts peak pulse power per line
 $t_p = 8/20 \mu s$
- Solid-state silicon-avalanche technology
- Protects one uni-directional I/O line
- Low clamping voltage
- Low leakage current
- High surge capability
- Meets moisture sensitivity level (MSL) 3
- Molding compound flammability rating: UL 94V-0
- Termination finish: Tin

Applications

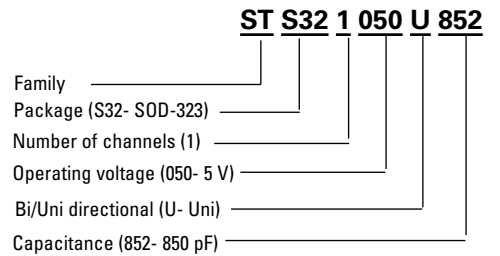
- Cellular handsets and accessories
- Microprocessor based equipment
- Potable electronics
- Notebooks, desktops, and servers
- Portable instrumentation
- Power lines
- Peripherals

Environmental compliance and general specifications

- IEC61000-4-2 (ESD)
 - Up to ± 30 kV (air)
 - Up to ± 30 kV (contact)
- IEC61000-4-5 (Lightning) Up to 110 A (8/20 μs)



Ordering part number



Pin out/functional diagram



SOD-323



Pin Configuration



Powering Business Worldwide

Absolute maximum ratings

(+25 °C, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value	Unit
STS32XXXXUXXX			
Peak pulse power dissipation on 8/20 μs waveform	P_{pp}	2000	W
ESD per IEC 61000-4-2 (Air)	V_{ESD}	+/-30	kV
ESD per IEC 61000-4-2 (Contact)		+/-30	
Lead soldering temperature	T_L	+260 (10 seconds)	°C
Operating junction temperature range	T_J	-55 to +125	°C
Storage temperature range	T_{STG}	-55 to +150	°C

Electrical characteristics

(+25 °C)

STS321050U852

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	5	V_{RWM} (V)
Reverse breakdown voltage	$I_t = 1$ mA	6	7	8	V_{BR} (V)
Reverse leakage current	$V_{RWM} = 5$ V	-	-	1	I_R (μA)
Clamping voltage	$I_{pp} = 50$ A, $t_p = 8/20$ μs	-	11	13	V_C (V)
		$I_{pp} = 110$ A, $t_p = 8/20$ μs	-	14	17
Junction capacitance	$V_{RWM} = 0$ V, $f = 1$ MHz	-	850	1050	C_J (pF)

STS321070U722

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	7	V_{RWM} (V)
Reverse breakdown voltage	$I_t = 1$ mA	7.5	8	9	V_{BR} (V)
Reverse leakage current	$V_{RWM} = 7$ V	-	-	1	I_R (μA)
Clamping voltage	$I_{pp} = 50$ A, $t_p = 8/20$ μs	-	12	15	V_C (V)
		$I_{pp} = 100$ A, $t_p = 8/20$ μs	-	15	18
Junction capacitance	$V_{RWM} = 0$ V, $f = 1$ MHz	-	720	900	C_J (pF)

Electrical characteristics
(+25 °C)

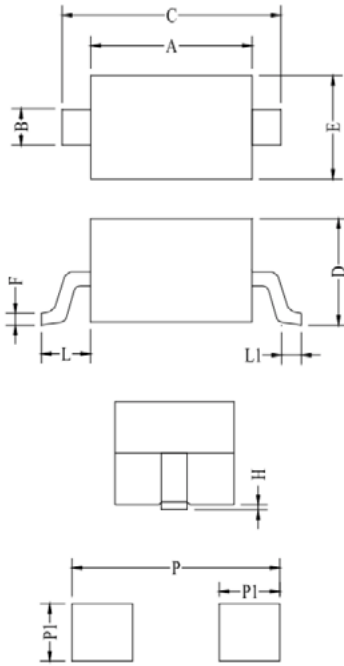
STS321120U372

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	12	V_{RWM} (V)
Reverse breakdown voltage	$I_t = 1$ mA	13	14.4	17	V_{BR} (V)
Reverse leakage current	$V_{RWM} = 12$ V	-	-	1	I_R (μ A)
Clamping voltage	$I_{PP} = 20$ A, $t_p = 8/20$ μ s	-	16	19	V_C (V)
	$I_{PP} = 40$ A, $t_p = 8/20$ μ s	-	20	24	V_C (V)
	$I_{PP} = 70$ A, $t_p = 8/20$ μ s	-	22	28	V_C (V)
	$t_p = 8/20$ μ s	-	-	-	V_C (V)
Junction capacitance	$V_{RWM} = 0$ V, $f = 1$ MHz	-	370	450	C_J (pF)

STS321150U332

Parameter	Test condition	Minimum	Typical	Maximum	Symbol (Units)
Reverse working voltage	-	-	-	15	V_{RWM} (V)
Reverse breakdown voltage	$I_t = 1$ mA	16	17.2	20	V_{BR} (V)
Reverse leakage current	$V_{RWM} = 15$ V	-	-	1	I_R (μ A)
Peak pulse current	$t_p = 8/20$ μ s	-	-	55	I_{PP} (A)
Clamping voltage	$I_{PP} = 25$ A, $t_p = 8/20$ μ s	-	22	25	V_C (V)
	$I_{PP} = 50$ A, $t_p = 8/20$ μ s	-	26	28	V_C (V)
	$I_{PP} = 55$ A, $t_p = 8/20$ μ s	-	27	30	V_C (V)
	$t_p = 8/20$ μ s	-	-	-	V_C (V)
Junction capacitance	$V_{RWM} = 0$ V, $f = 1$ MHz	-	330	400	C_J (pF)

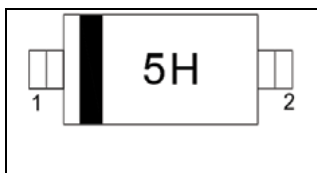
Mechanical parameters, pad layout- mm/inches



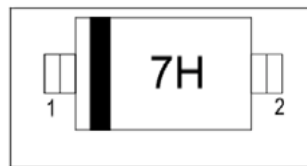
Dimension	Millimeters		Inches	
	Minimum	Maximum	Minimum	Maximum
A	1.60	1.80	0.063	0.071
B	0.25	0.35	0.010	0.014
C	2.50	2.75	0.098	0.108
D	0.00	1.00	0.000	0.039
E	1.20	1.40	0.047	0.055
F	0.08	0.15	0.003	0.006
L	0.475 REF		0.019 REF	
L1	0.25	0.40	0.010	0.016
H	0.00	0.10	0.000	0.004
P	3.00	3.00	0.118	0.118
P1	0.80	0.80	0.031	0.031

Land Pattern

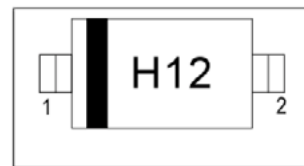
Part marking



(STS321050U852)



(STS321070U722)



(STS321120U372)

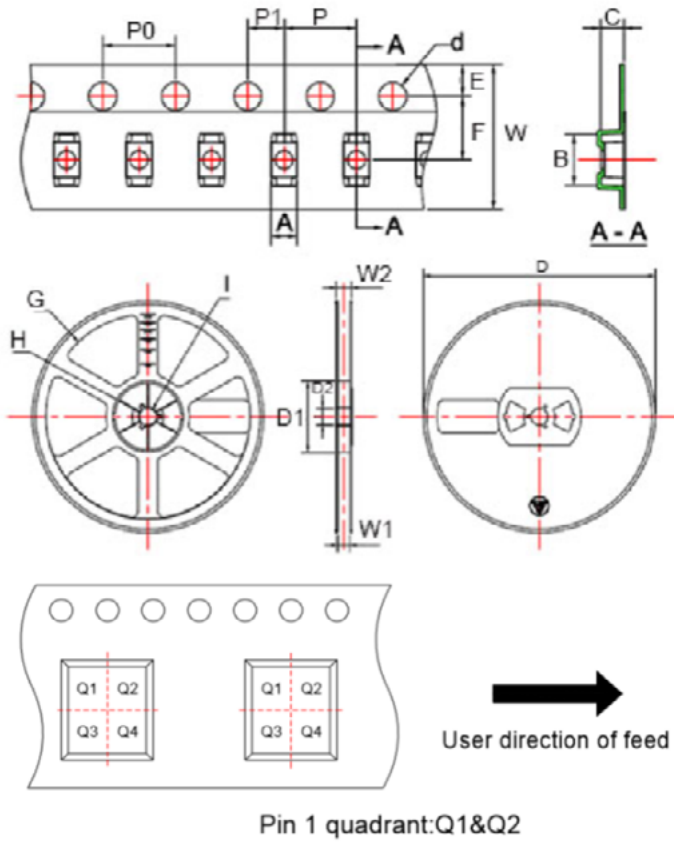


(STS321150U332)

Packaging information mm/inches

Drawing not to scale.

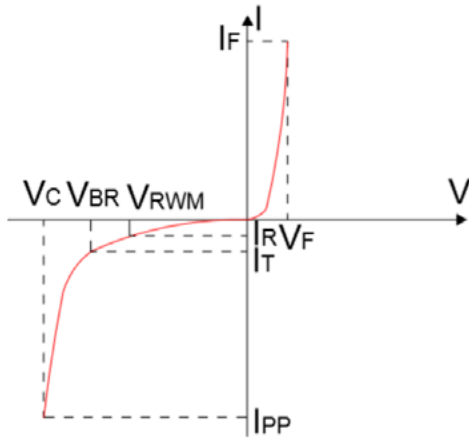
Supplied in tape and reel packaging, 3,000 parts per 7" diameter reel (EIA-481 compliant)



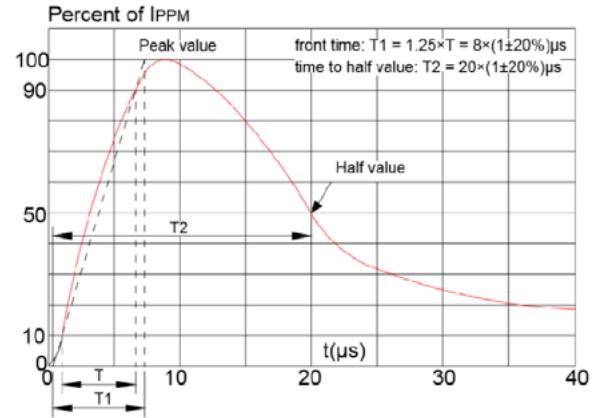
Symbol	Millimeters	Inches
A	1.46±0.05	0.057±0.002
B	2.90±0.05	0.114±0.002
C	1.25±0.05	0.049±0.002
d	±1.50±0.1	±0.059±0.004
E	1.75±0.1	0.069±0.004
F	3.50±0.1	0.138±0.004
P0	4.0±0.1	0.157±0.004
P	4.0±0.1	0.157±0.004
P1	2.0±0.1	0.079±0.004
W	8.00+0.3/-0.1	0.315+0.012/-0.004
D	±178.0±2	±7.008±0.079
D1	54.40±1	2.142±0.039
D2	13.0±1	0.512±0.039
G	R78.0±1	R3.071±0.039
H	R25.60±1	R1.008±0.039
I	R6.50±1	R0.256±0.039
W1	9.50±1	0.374±0.039
W2	12.30±1	0.484±0.039

Ratings and V-I characteristic curves (+25 °C unless otherwise noted)

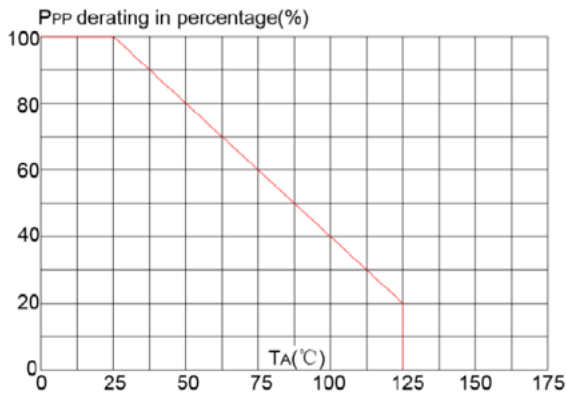
V- I curve characteristics (Uni-directional)



Pulse waveform (8/20 μ s)



Pulse derating curve



ESD waveform

